

# Final Product/Process Change Notification

Document #:FPCN23715Z Issue Date:12 Jan 2021

Title of Change:	NCV8774 family – Wafer Technology, Wafer Fab location and Package upgrades				
Proposed Changed Material First Ship Date:	13 Jan 2022 or earlier if approved by customer				
Current Material Last Order Date:	31 Jul 2021  Orders received after the Current Material Last Order Date expiration are to be considered as orders for new changed material as described in this PCN. Orders for current (unchanged, material after this date will be per mutual agreement and current material inventory availability.				
Current Material Last Delivery Date:	12 Jan 2022 unless otherwise mutually agreed The Current Material Last Delivery Date may be subject to change based on build and depletion of the current (unchanged) material inventory				
Product Category:	Active components – Integrated circuits				
Contact information:	Contact your local ON Semiconductor Sales Office or Juraj.Kremmer@onsemi.com				
PCN Samples Contact:	Contact your local ON Semiconductor Sales Office to place sample order or <pcn.samples@onsemi.com>.  Sample requests are to be submitted no later than 45 days after publication of this change notification.  Samples delivery timing will be subject to request date, sample quantity and special customer packing/label requirements.</pcn.samples@onsemi.com>				
Sample Availability Date:	1 Jan 2021				
PPAP Availability Date:	26 Feb 2021				
Additional Reliability Data:	Contact your local ON Semiconductor Sales Office or Tomas.Vajter@onsemi.com				
Type of Notification:	This is a Final Product/Process Change Notification (FPCN) sent to customers. FPCNs are issued 12 months prior to implementation of the change or earlier upon customer approval. ON Semiconductor will consider this proposed change and it's conditions acceptable, unless an inquiry is made in writing within 45 days of delivery of this notice. To do so, contact PCN.Support@onsemi.com.				
Change Category					
Category	Type of Change				
Design	Design Change in Active Elements				
Data Sheet	Change of datasheet parameters/electrical specification (min./max./typ. values) and/or AC/DC specification				
Process - Wafer Production	Move of all or part of wafer fab to a different location/site/subcontractor Change in process technology (e. g. process changes like lithography, etch, oxide deposition, diffusion, die back surface preparation/backgrind,), New wafer diameter				
Change of wire bonding, Process - Assembly Change of mold compound, Change of product marking					

## **Description and Purpose:**

Change of wafer processing technology from PS5B currently manufactured in Fab2, Oudenaarde, Belgium (150 mm fab) to I3T50 in Gresham, Oregon, USA (200 mm fab). Old PS5B technology replaced by the more advanced I3T50 wafer process. PS5B wafer technology is nearing end of life and cannot support future production needs.

These changes are also related to the Fab2 manufacturing site sale.

Design changes done in order to support the new wafer technology.

In addition, package changes were done to improve delamination performance.

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	Before Change Description	After Change Description		
OPN	NCV8774DT50RKG, NCV8774DT33RKG	NCV8774CDT50RKG, NCV8774CDT33RKG		
Wafer Fab location	Fab2, Oudenaarde, Belgium	Gresham, Oregon, USA		
Wafer Technology	PS5B (1.5um)	I3T50 (0.35um)		
Wafer Diameter	150mm	200mm		
Bond Wire	Cu 2.0 mil	Cu 1.5 mil		
Mold Compound	GE 8000CH4ES	G700HF		

	From	То
Drodust marking change	NCV8774DT50RKG - Line1: 877450G	NCV8774CDT50RKG - Line1: 8774C5G
Product marking change	NCV8774DT33RKG - Line1: 877433G	NCV8774CDT33RKG - Line1: 8774C3G

## Reason / Motivation for Change:

**Benefit of the change:** More modern wafer technology that will supported long term with improved wafer fab capacity. Improved package BOM.

Risk for Late Release: Possible supply disruptions.

Quality Improvement: Yes. Lower die defectivity, improved package delamination performance.

Anticipated impact on fit, form, function, reliability, product safety or manufacturability:

The device has been qualified and validated based on the same Product Specification. The device has successfully passed the qualification tests. Potential impacts can be identified, but due to testing performed by ON Semiconductor in relation to the PCN, associated risks are verified and excluded.

Datasheet updates as shown in Electrical Characteristic Summary below.

#### **Sites Affected:**

ON Semiconductor Sites	External Foundry/Subcon Sites
ON Semiconductor Oudenaarde, Belgium	None
ON Semiconductor Gresham, Oregon, USA	
ON Semiconductor Seremban, Malaysia	

# Marking of Parts/ Traceability of Change:

New part numbers will have a new package topside marking:

NCV8774CDT50RKG - Line1: 8774C5G; NCV8774CDT33RKG - Line1: 8774C3G.

## **Reliability Data Summary:**

QV DEVICE NAME: NCV8774CDT50RKG, NCV8774CDT33RKG

RMS: S59632

PACKAGE: DPAK 5LD

Test	Specification	Specification Condition		Results	
HTOL	JESD22-A108	Ta = 125°C, Vcc = 40V	2016 hrs	0/240	
HTSL	JESD22-A103	Ta = 150°C	2016 hrs	0/252	
TC	JESD22-A104	Ta = -65°C to+150°C	1000 cyc	0/252	
PTC	JESD22 A105	Ta = -40°C to+125°C	1000 cyc	0/55	
HAST	JESD22-A110	Ta = 110°C, 85% RH, 18.8psig, Vcc = 40V	528 hrs	0/252	
uHAST	JESD22-A118	Ta = 130°C, 85% RH, 18.8psig, unbiased	192 hrs	0/252	
PC	J-STD-020 JESD-A113	MSL= 1 @ 260°C			

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SD JSTD002	Ta = 245C, 5 sec		0/15
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#### NOTE: AEC-1pager is attached.

To view attachments:

- 1. Download pdf copy of the PCN to your computer
- 2. Open the downloaded pdf copy of the PCN
- 3. Click on the paper clip icon available on the menu provided in the left/bottom portion of the screen to reveal the Attachment field
- 4. Then click on the attached file.

## **Electrical Characteristics Summary:**

### Datasheet Parametric Table Updated as Follows

			NCV8774C			NCV8774					
$V_{ln}=13.5~V,~~C_{ln}=0.1~\mu\text{F},~~C_{cut}=1~\mu\text{F},$ ELECTRICAL CHARACTERISTICS Min and Max values are valid for temperature									noted		
			noted otherwise and are guaranteed by test, d Typical values are referenced to T, = 25°C	esign or stati	istical corre	elation.	otherwise and are guaranteed by test, design Typical values are referenced to T <sub>J</sub> = 25°C	or statistica	al correlation	on.	
Parameter		Symbol	Test Conditions	Min	Тур	Max	Test Conditions	Min	Тур	Max	U
Output Voltage		Yout		(-2%)		(+2%)		(-2%)		(+2%)	
	3.3 V		V <sub>in</sub> = 4.5 V to 40 V, I <sub>out</sub> = 0.1 mA to 200 mA	3.234	3.3	3.366	V <sub>in</sub> = 4.5 V to 40 V, I <sub>out</sub> = 0.1 mA to 200 mA	3.234	3.3	3.366	
	3.3 V		V <sub>in</sub> = 4.5 V to 16 V, I <sub>out</sub> = 0.1 mA to 350 mA	3.234	3.3	3.366	V <sub>in</sub> = 4.5 V to 16 V, J <sub>out</sub> = 0.1 mA to 350 mA	3.234	3.3	3.366	
	5.0 V		V <sub>in</sub> = 5.45 V to 40 V, J <sub>out</sub> = 0.1 mA to 200 mA	4.9	5.0	5.1	V <sub>in</sub> = 5.6 V to 40 V, J <sub>out</sub> = 0.1 mA to 200 mA	4.9	5.0	5.1	
	5.0 V		V <sub>in</sub> = 5.7 V to 16 V, J <sub>out</sub> = 0.1 mA to 350 mA	4.9	5.0	5.1	V <sub>in</sub> = 5.975 V to 16 V, J <sub>out</sub> = 0.1 mA to 350 mA	4.9	5.0	5.1	
	3.3 V		V <sub>in</sub> = 4.5 V to 40 V, I <sub>out</sub> = 0 mA	3.234	3.3	3.366	V <sub>in</sub> = 4.5 V to 28 V, I <sub>out</sub> = 0 mA to 350 mA	3.234	3.3	3.366	
	5.0 V		V <sub>in</sub> = 5.45 V to 40 V, I <sub>out</sub> = 0 mA	4.9	5.0	5.1	V <sub>in</sub> = 5.975 V to 28 V, I <sub>out</sub> = 0 mA to 350 mA	4.9	5.0	5.1	
Dropout Voltage		V <sub>DO</sub>									r
	3.3 V		J <sub>out</sub> = 200 mA	-	200	350	I <sub>out</sub> = 200 mA	-	250	500	r
	5.0 V		J <sub>out</sub> = 350 mA	-	350	600	l <sub>out</sub> = 350 mA	-	440	875	
Parameter		Symbol	Test Conditions	Min	Typ	Max	Test Conditions	Min	Tvp	Max	U
Quiescent Current (lှ =	= I <sub>in</sub> — I <sub>out</sub> )	Į <sub>a</sub>									
	w w.	~	J <sub>out</sub> = 0 mA, T <sub>J</sub> = 25 °C	_	17	21					'
			J <sub>out</sub> = 0 mA, T <sub>J</sub> ≤ 125 °C	_	_	23					
			J <sub>out</sub> = 0.1 mA, T <sub>J</sub> = 25 °C	_	19	23	J <sub>out</sub> = 0.1 mA, T <sub>J</sub> = 25 °C	_	18	22	
			J <sub>out</sub> = 0.1 mA, T <sub>1</sub> ≤ 125 °C	-	-	25	J <sub>out</sub> = 0.1 mA to 350 mA, T <sub>J</sub> ≤ 125 °C	_	-	23	
Power Supply Ripple R	ejection	PSRR					- ***				Ħ
			f = 100 Hz, 0.5 V <sub>pp</sub>	-	80	-	f = 100 Hz, 0.5 V <sub>pp</sub>	-	54	-	

#### **List of Affected Parts:**

**Note:** Only the standard (off the shelf) part numbers are listed in the parts list. Any custom parts affected by this PCN are shown in the customer specific PCN addendum in the PCN email notification, or on the <u>PCN Customized Portal</u>.

Current Part Number	New Part Number	Qualification Vehicle
NCV8774DT33RKG	NCV8774CDT33RKG	NCV8774CDT50RKG
NCV8774DT50RKG	NCV8774CDT50RKG	NCV8774CDT50RKG

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